

RL78/I1A

RENESAS MCU

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True Low Power Platform (as low as 156.25 μ A/MHz, and 0.60 μ A for RTC + LVD), 2.7 V to 5.5 V operation, 32 to 64 Kbyte Flash, for Lighting Control Applications

1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 2.7 V to 5.5 V operation from a single supply
- Stop (RAM retained): 0.23 μA, (LVD enabled): 0.31 μA
- Halt (RTC + LVD): 0.60 μA
 Operating: 156.25 μA/MHz

16-bit RL78 CPU Core

- Delivers 41 DMIPS at maximum operating frequency of 32 MHz
- Instruction Execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC Architecture (Harvard) with 3-stage pipeline
- Multiply Signed & Unsigned: 16 x 16 to 32-bit result in 1 clock cycle
- MAC: 16 x 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Main Flash Memory

- Density: 32 KB to 64 KB
- Block size: 1 KB
- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory

- Data Flash with background operation
- Data flash size: 4 KB
- Erase Cycles: 1 Million (typ.)
- Erase/programming voltage: 2.7 V to 5.5 V

RAM

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- 2 KB to 4 KB size options
- · Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator

- 32 MHz with +/- 1% accuracy over voltage (2.7 V to 5.5 V) and temperature (-20 °C to 85 °C)
- Pre-configured settings: 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 4 MHz & 1 MHz

Reset and Supply Management

- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 6 setting options (Interrupt and/or reset function)

Data Memory Access (DMA) Controller

- Up to 2 fully programmable channels
- Transfer unit: 8- or 16-bit

16-bit timers KB0 to KB2, and KC0 for PWM output

16-bit timers KB0 to KB2: maximum 6 outputs (3 ch × 2)

- Smooth start function, dithering function, forced output stop function (unsyncronized with comparator or external interrupt), and interleave PFC function
- Average resolution < 1 nsec output, 64 MHz (when using PLL) + dithering option

16-bit timer KC0 (3 ch)

 PWM output gating function by interlocking with 16bit timers KB0, KB1, and KB2

Extended-Function Timers

- Multi-function 16-bit timers: Up to 8 channels
- Real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- Interval Timer: 12-bit, 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Multiple Communication Interfaces

- Up to 1 x I²C multi-master (SM/PM bus support)
- Up to 1 x CSI/SPI (7-, 8-bit)
- Up to 3 x UART (7-, 8-, 9-bit), DALI Support 1ch
- Up to 1 x LIN

Rich Analog

- ADC: Up to 11 channels, 8/10-bit resolution, 2.125 μ s conversion time
- Supports 2.7 V
- Internal voltage reference (1.45 V)
- Comparator: Up to 6 channels, Internal DAC 3ch 8bit resolution, window comparator mode
- PGA (x4 to x32):6 input
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)

- Flash memory CRC calculation
- RAM parity error check
- RAM/SFR write protection
- Illegal memory access detection
- Clock stop/ frequency detection
- ADC self-test

General Purpose I/O

- 5V tolerant, high-current (up to 8.5 mA per pin)
- Open-Drain, Internal Pull-up support

Operating Ambient Temperature

- Standard: -40 °C to +105 °C
- Extend: -40 °C to +125 °C

Package Type and Pin Count

SSOP: 20, 30, 38



O ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/I1A				
			20 pins	30 pins	38 pins		
64 KB	4 KB	4 KB Note	-	- R5F107AE R5F107			
32 KB	4 KB	2 KB	R5F1076C				

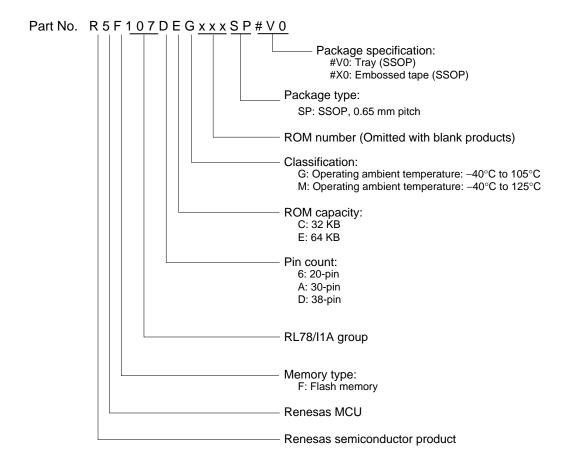
Note This is about 3 KB when the self-programming function and data flash function are used.

<R> 1.2 Ordering Information

Pin count	Package	Operating ambient	Part Number
		temperature	
20 pin	20-pin plastic SSOP	$T_A = -40 \text{ to } +105^{\circ}\text{C}$	R5F1076CGSP#V0, R5F1076CGSP#X0
	(4.4 x 6.5)	$T_A = -40 \text{ to } +125^{\circ}\text{C}$	R5F1076CMSP#V0, R5F1076CMSP#X0
30 pin	30-pin plastic SSOP	$T_A = -40 \text{ to } +105^{\circ}\text{C}$	R5F107ACGSP#V0, R5F107AEGSP#V0,
00 p	(7.62 mm (300))		R5F107ACGSP#X0, R5F107AEGSP#X0
		$T_A = -40 \text{ to } +125^{\circ}\text{C}$	R5F107ACMSP#V0, R5F107AEMSP#V0,
			R5F107ACMSP#X0, R5F107AEMSP#X0
38 pin	38-pin plastic SSOP	$T_A = -40 \text{ to } +105^{\circ}\text{C}$	R5F107DEGSP#V0, R5F107DEGSP#X0
'	(7.62 mm (300))	$T_A = -40 \text{ to } +125^{\circ}\text{C}$	R5F107DEMSP#V0, R5F107DEMSP#X0

Caution The RL78/I1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

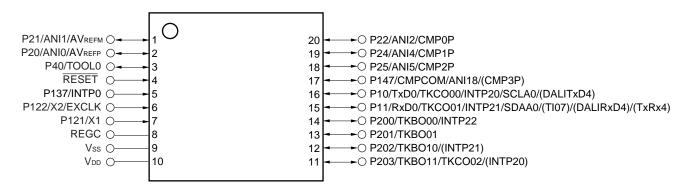
Figure 1-1. Part Number, Memory Size, and Package of RL78/I1A



1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic TSSOP (4.4 x 6.5)



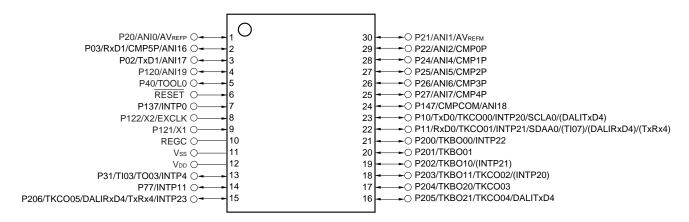
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC).
- **3.** The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).

1.3.2 30-pin products

• 30-pin plastic SSOP (7.62 mm (300))

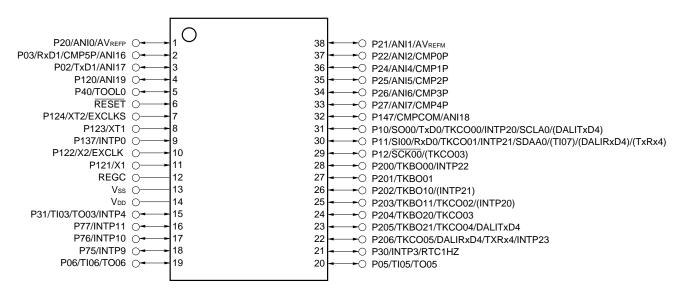


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC).

1.3.3 38-pin products

• 38-pin plastic SSOP (7.62 mm (300))



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC).

1.4 Pin Identification

ANI0 to ANI2, REGC: Regulator Capacitance

ANI4 to ANI7, RESET: Reset

ANI16 to ANI19: Analog Input RTC1HZ: Real-time Clock Correction Clock

AVREFM: Analog Reference Voltage Minus (1 Hz) Output

AVREFP: Analog Reference Voltage Plus RxD0, RxD1,

CMP0P to CMP5P: Comparator Analog Input DALIRxD4: Receive Data

CMPCOM: Comparator External Reference SCK00: Serial Clock Input/Output

Voltage SCLA0: Serial Clock Input/Output

EXCLK: External Clock Input (Main System SDAA0: Serial Data Input/Output

Clock) SI00: Serial Data Input

EXCLKS: External Clock Input (Subsystem SO00: Serial Data Output

Clock) TI03, TI05, TI06,

<R> INTP0, INTP3, Timer Input

INTP4, INTP9, T003, T005, T006, INTP10, INTP11, TKB000, TKB001 to

INTP20 to INTP23: Interrupt Request from Peripheral TKBO20, TKBO21,

P02, P03, TKCO00-TKCO05: Timer Output

P05, P06: Port 0 TOOL0: Data Input/Output for Tool

P10 to P12: Port 1 TxRx4: Serial Data Input/Output for Single

P20 to P22, Wired UART

P24 to P27: Port 2 TxD0, TxD1

Port 20

P30, P31: Port 3 DALITxD4: Transmit Data
P40: Port 4 VDD: Power Supply

P75 to P77: Port 7 Vss: Ground

P120 to P124: Port 12 X1, X2: Crystal Oscillator (Main System Clock)

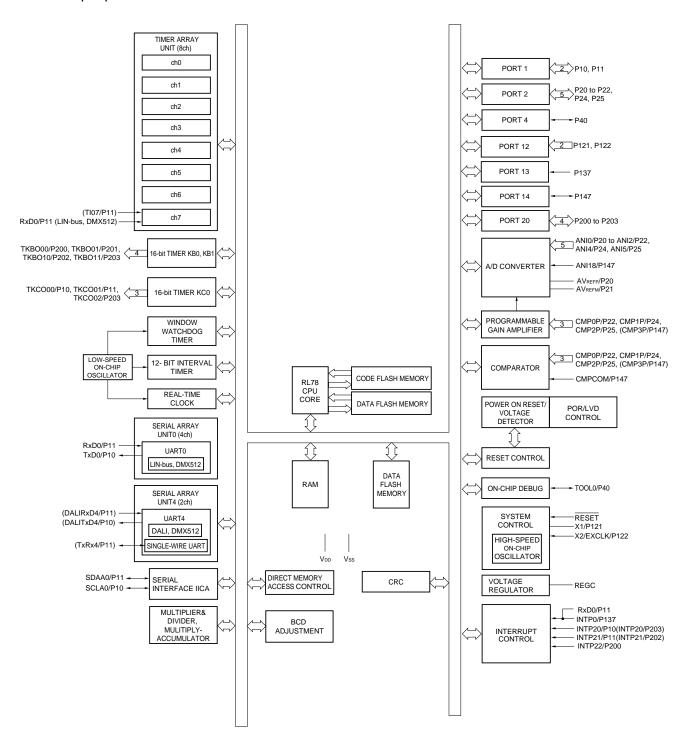
P137: Port 13 XT1, XT2: Crystal Oscillator (Subsystem Clock)

P147: Port 14

P200 to P206:

1.5 Block Diagram

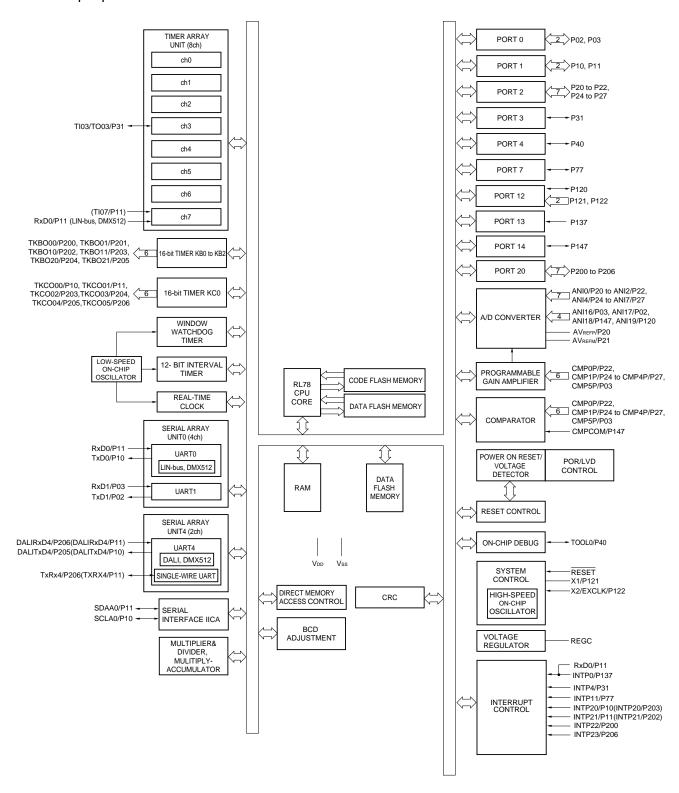
1.5.1 20-pin products



Remarks 1. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC).

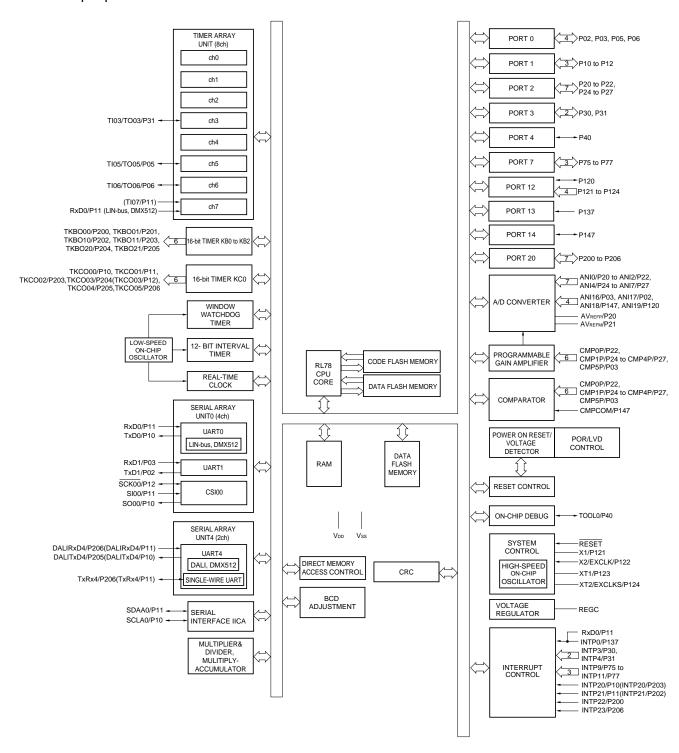
2. The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).

1.5.2 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC).

1.5.3 38-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC).

1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR1) is set to 00H.

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						\ /		
		Item	20-pin	30	-pin	38-pin		
			R5F1076C	R5F107AC	R5F107AE	R5F107DE		
	Code flash me	emory (KB)	32	32	64	64		
	Data flash me	mory (KB)	4	4	4	4		
	RAM (KB)		2	2	4 ^{Note 1}	4 ^{Note 1}		
	Memory space	е	1 MB		<u>. </u>			
	Main system clock	High-speed system clock	X1 (crystal/ceramic) osc 1 to 20 MHz: V _{DD} = 2.7		ystem clock input (EXCLK)			
		High-speed on-chip oscillator	HS (High-speed main) r LS (Low-speed main) m	mode: 1 to 32 MHz (V _{DD} and e: 1 to 8 MHz (V _{DD} =				
<r></r>	Clock for 16-b and KC0	it timers KB0 to KB2,	64 MHz (TYP.)					
<r></r>	Subsystem cloonly)	ock (38-pin products	XT1 (crystal) oscillation 32.768 kHz	, external subsystem clo	ck input (EXCLKS)			
<r></r>	Low-speed on	-chip oscillator	15 kHz (TYP.)					
<r></r>	General-purpo	ose register	(8-bit register × 8) × 4 banks					
	Minimum instr	ruction execution time	0.03125 μ s (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)					
			$0.05~\mu s$ (High-speed system clock: $f_{MX} = 20~MHz$ operation)					
			30.5 μ s (Subsystem clock: fsuB = 32.768 kHz operation) (38-pin products only)					
	Instruction set		8-bit operation, 16-bit Multiplication (8 bits > Bit manipulation (Set,	•	n operation), etc.			
	I/O port	Total	16		26	34		
		CMOS I/O	13		23	29		
		CMOS input	3		3	5		
		CMOS output	-		-	_		
	Timer 16-bit timer TAU		Timer 16-bit timer TAU 8 channels (no timer output: 1, PWM output: 1 Note 2) output)					
		16-bit timer KB	2 channels (PWM outputs: 4)	3	channels (PWM outputs: 6	()		
		16-bit timer KC	1 channel (PWM outputs: 3)	1	channel (PWM outputs: 6))		

Notes 1. This is about 3 KB when the self-programming function and data flash function are used. (For details, see **CHAPTER 3**)

2. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves). (see 6.8.3 Operation as multiple PWM output function).

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	Item		20-pin	30-pin	38-pin			
			R5F1076C	R5F107AC, R5F107AE	R5F107DE			
Timer	Natchdo	g timer	1 channel					
	Real-time clock (RTC)			1 channel ^{Notes 1, 2}				
	12-bit inte IT)	erval timer		1 channel				
	RTC outp	out		-	1 1 Hz (subsystem clock f _{SUB} = 32.768 kHz)			
8/10-bit resoluti	on A/D co	onverter	6 channels	11 channels	11 channels			
Comparator			4 channels	6 channels	6 channels			
Programmable	gain amp	lifier		1 channel				
		Input ^{Note 3}	4 channels	6 channels	6 channels			
Serial interface			[20-pin]		1			
				N-bus and DMX512): 1 channel				
				ALI communication): 1 channel				
			[30-pin products]					
			UART (Supporting LIN-bus and DMX512): 1 channel					
			UART: 1 channel					
			UART (Supporting DALI communication): 1 channel					
			[38-pin products]					
			 CSI: 1 channel/UART (Supporting LIN-bus and DMX512): 1 channel UART: 1 channel 					
	-2			ALI communication): 1 channel				
	I ² C b		1 channel	1 channel	1 channel			
Multiplier and d accumulator	vider/mu	ltiply-	 • 16 bits × 16 bits = 32 bits (Unsigned or signed) • 32 bits ÷ 32 bits = 32 bits (Unsigned) • 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 					
DMA controller				2 channels				
Vectored interru	ıpt Interi	nal	27	30	30			
sources	Exte		7	10	11			
Reset			Reset by RESET pin Internal reset by watce Internal reset by power Internal reset by voltae Internal reset by illegae Internal reset by RAM	er-on-reset age detector al instruction execution ^{Note 4}				
			Internal reset by illegal-memory access					

Notes 1. The subsystem clock (fsub) can be selected as the operating clock only for 38-pin products.

- 2. The 20- and 30-pin products can only be used as the constant-period interrupt function.
- 3. The comparator input is alternatively used with analog input pin (ANI pin).
- 4. The illegal instruction is generated when instruction code FFH is executed.
 Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

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Item	20-pin	30-pin	38-pin
	R5F1076C	R5F107AC, R5F107AE	R5F107DE
Power-on-reset circuit	Power-on-reset: 1. Power-down-reset: 1.	.51 ±0.03 V .50 ±0.03 V	
Voltage detector		V to 4.06 V (6 stages) V to 3.98 V (6 stages)	
On-chip debug function	Provided		
Power supply voltage	V _{DD} = 2.7 to 5.5 V		
Operating ambient temperature	$T_A = -40 \text{ to } +105^{\circ}\text{C}$ $T_A = -40 \text{ to } +125^{\circ}\text{C}$		

2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +105°C)

Target products : $T_A = -40 \text{ to } +105^{\circ}\text{C}$

R5F1076CGSP#V0, R5F1076CGSP#X0, R5F107ACGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#V0, R5F107AEGSP#X0, R5F107DEGSP#V0, R5F107DEGSP#X0

Caution

The RL78/I1A have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		−0.5 to +6.5	V
REGC pin input voltage	Virego	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VII	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo ₁	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	VAI1	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)} + 0.3 V$ in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF(+)}$: + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins	P02, P03, P40, P120	-70	mA
		-170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	І он2	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins	P02, P03, P40, P120	70	mA
		170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	lo _{L2}	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +105	°C
temperature		In flash memory	programming mode		
Storage temperature	T _{stg}			-65 to +150	°C

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2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Recommended Circuit	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator	Vss X1 X2 Rd		1.0		20.0	MHz
XT1 clock oscillation frequency (fxt) ^{Note}	Crystal resonator	Vss XT2 XT1 Rd C4 C3 T		32	32.768	35	kHz

- Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

2.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

<u> </u>						
Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Note 1	fıн		1		32	MHz
High-speed on-chip oscillator		$T_A = -20 \text{ to } 85^{\circ}\text{C}$	-1		+1	%
clock frequency accuracy Note 2		$T_A = -40 \text{ to } 105^{\circ}\text{C}$	-1.5		+1.5	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - **2.** This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

2.2.3 PLL Characteristics

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	f _{PLLIN}	High-speed system clock is selected (f _{MX} = 4 MHz)	3.94	4.00	4.06	MHz
frequency Note		High-speed on-chip oscillator clock is selected (fiн = 4 MHz)	3.94	4.00	4.06	MHz
PLL output clock frequency Note	fPLL			fpllin × 16		MHz

Note This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	Іон1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			-1.0	mA
		(Mhan duty < 700/ Note 3)	$4.0~V \leq V_{DD} \leq 5.5~V$			-12.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			-4.0	mA
		P75 to P77 P147 P200 to P206	$4.0~V \leq V_{DD} \leq 5.5~V$			-30.0	mA
			$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} < 4.0~\textrm{V}$			-10.0	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			-30.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			-14.0	mA
Іон2	І он2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			-0.7	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoH × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	lo _{L1}	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{DD} \leq 5.5~V$			8.5 ^{Note 2}	mA
low ^{Note 1}		P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$			1.5 ^{Note 2}	mA
		Total of P02, P03, P40, P120 (When duty ≤ 70% ^{Note 3})	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			7.5	mA
	Total of P05, P06, P10 to P12, P30,	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA	
		P31, P75 to P77, P147, P200 to P206 (When duty \leq 70% Note 3) Total of all pins (When duty \leq 70% Note 3)	$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$			17.5	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			80.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			25.0	mA
loı	lo _{L2}	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			0.4 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% Note 3)	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$			2.8	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and lol = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8V _{DD}		V _{DD}	>
	V _{IH2}	P03, P10, P11	TTL input buffer $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	2.1		V _{DD}	V
			TTL input buffer $3.3 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	2.0		V _{DD}	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		V _{DD}	V
Input voltage, low	V _{IL1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40,P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	V
	VIL2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0		0.8	V
			TTL input buffer 3.3 V ≤ V _{DD} < 4.0 V	0		0.5	V
			TTL input buffer $2.7 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}$	0		0.32	V

Cautions The maximum value of V_{IH} of pins P02, P10 to P12 is V_{DD}, even in the N-ch open-drain mode.

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
high	Vон1	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	V _{DD} - 0.7			V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OH1}} = -1.0 \text{ mA}$	V _{DD} - 0.5			V
	V _{OH2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \ \mu\text{A}$	V _{DD} - 0.5			V
Output voltage, low	Vol1	P31, P40, P75 to P77, P120, P147, P200 to P206	$4.0~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 8.5~mA$			0.7	V
			$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 4.0 \text{ mA}$			0.4	V
			$2.7~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
	V _{OL2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $\text{I}_{OL2} = 400 \ \mu\text{A}$			0.4	V

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Condition	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ілн1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	VI = VDD				1	μΑ
	ILIH2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)		In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low	ILIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	Vı = Vss				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μА
				In resonator connection			-10	μΑ
On-chip pll-up resistance	Rυ	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	V _I = Vss, In input port		10	20	100	kΩ

2.3.2 Supply current characteristics

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V) (1/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	fih = 32 MHz ^{Note 3}	V _{DD} = 5.0 V		5.0	7.5	mA
current ^{Note 1}		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		5.0	7.5	mA
			mode	f _{IH} = 24 MHz ^{Note 3}	V _{DD} = 5.0 V		3.9	5.8	mA
					V _{DD} = 3.0 V		3.9	5.8	mA
				fih = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.2	mA
					V _{DD} = 3.0 V		2.9	4.2	mA
			LS (low-	fih = 8 MHz ^{Note 3} ,	V _{DD} = 3.0 V		1.3	2.0	mA
			speed main) mode ^{Note 5}	$TA = -40 \text{ to } + 85^{\circ}C$					
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Square wave input		3.2	4.9	mA
			speed main) mode ^{Note 5}	$V_{DD} = 5.0 \text{ V}$	Resonator connection		3.3	5.0	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Square wave input		3.2	4.9	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.0	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Square wave input		2.0	2.9	mA
				$V_{DD} = 5.0 \text{ V}$	Resonator connection		2.0	2.9	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Square wave input		2.0	2.9	mA
				V _{DD} = 3.0 V	Resonator connection		2.0	2.9	mA
			LS (low-	$f_{MX} = 8 \text{ MHz}^{\text{Note 2}},$	Square wave input		1.2	1.8	mA
			speed main) mode ^{Note 5}	$V_{DD} = 3.0 \text{ V},$ $T_{A} = -40 \text{ to } + 85^{\circ}\text{C}$	Resonator connection		1.2	1.8	mA
			HS (high- speed main) mode ^{Note 5}	$f_{IH} = 4 \text{ MHz}^{\text{Note 3}}$ $f_{PLL} = 64 \text{ MHz}, f_{CLK} = 32 \text{ MHz}$	V _{DD} = 5.0 V		5.4	8.5	mA
					V _{DD} = 3.0 V		5.4	8.5	mA
				f _{IH} = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		3.3	5.7	mA
				fpll = 64 MHz, fclk = 16 MHz	V _{DD} = 3.0 V		3.3	5.7	mA
			Subsystem	fsub = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μΑ
			clock operation	$T_A = -40^{\circ}C$	Resonator connection		4.4	6.2	μΑ
			operation	fsub = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μΑ
				T _A = +25°C	Resonator connection		4.4	6.2	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μΑ
				T _A = +50°C	Resonator connection		4.5	7.4	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μΑ
				T _A = +70°C	Resonator connection		4.6	8.3	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μΑ
				T _A = +85°C	Resonator connection		5.4	11.6	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μΑ
				$T_A = +105^{\circ}C$	Resonator connection		7.1	21.0	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz to } 32 \text{ MHz}$ LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz to } 8 \text{ MHz}$

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(Ta = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V) (2/2)

Parameter	Symbol			Conditions	_	MIN.	TYP.	MAX.	Unit
Supply	IDD2 ^{Note 2}	HALT	HS (high-	fih = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.72	2.9	mA
current ^{Note 1}		mode	speed main) mode ^{Note 7}		V _{DD} = 3.0 V		0.72	2.9	mA
			mode	fih = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.57	2.3	mA
					V _{DD} = 3.0 V		0.57	2.3	mA
				fih = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.7	mA
					V _{DD} = 3.0 V		0.50	1.7	mA
			LS (low- speed main) mode ^{Note 7}	$f_{IH} = 8 \text{ MHz}^{\text{Note 4}},$ $T_{A} = -40 \text{ to } +85^{\circ}\text{C}$	V _{DD} = 3.0 V		320	910	μА
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	1.9	mA
			speed main) mode ^{Note 7}	V _{DD} = 5.0 V	Resonator connection		0.50	2.0	mA
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	1.9	mA
				VDD = 3.0 V	Resonator connection		0.50	2.0	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.24	1.02	mA
				VDD = 5.0 V	Resonator connection		0.30	1.08	mA
			$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.24	1.02	mA	
				V _{DD} = 3.0 V	Resonator connection		0.30	1.08	mA
			LS (low-	$f_{MX} = 8 MHz^{Note 3},$	Square wave input		130	720	μА
			speed main) mode ^{Note 7}	$V_{DD} = 3.0 \text{ V},$ $T_{A} = -40 \text{ to } +85^{\circ}\text{C}$	Resonator connection		170	760	μA
			HS (high-	f⊩ = 4 MHz ^{Note 4}	V _{DD} = 5.0 V		1.15	4.0	mA
			speed main) mode ^{Note 7}	$f_{PLL} = 64 \text{ MHz}, f_{CLK} = 32 \text{ MHz}$	V _{DD} = 3.0 V		1.15	4.0	mA
			mode	f _H = 4 MHz ^{Note 4}	V _{DD} = 5.0 V		0.95	3.2	mA
				fPLL = 64 MHz, fcLK = 16 MHz	V _{DD} = 3.0 V		0.95	3.2	mA
			Subsystem clock operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.70	μА
				T _A = -40°C	Resonator connection		0.47	0.89	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.33	0.70	μА
				T _A = +25°C	Resonator connection		0.52	0.89	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.41	1.90	μA
				T _A = +50°C	Resonator connection		0.60	2.09	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.54	2.80	μA
				T _A = +70°C	Resonator connection		0.73	2.99	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.27	6.10	μА
				T _A = +85°C	Resonator connection		1.46	6.29	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		3.04	15.5	μA
				T _A = +105°C	Resonator connection		3.23	15.7	μА
	IDD3 ^{Note 6}	STOP	T _A = -40°C				0.18	0.50	μA
		mode ^{Note 8}	T _A = +25°C				0.23	0.50	μΑ
			T _A = +50°C				0.27	1.70	μΑ
			T _A = +70°C				0.44	2.60	μΑ
		I 📙	T _A = +85°C				1.17	5.90	μΑ
			T _A = +105°C			2.94	15.3	μА	

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - **4.** When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **6.** Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 8 MHz

- **8.** Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



<R>

<R> $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Danagerites	Combal		,		NAINI	TVD	MAN	11-2
Parameter	Symbol		Condition	ons	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	IFIL Note 1					0.20		μΑ
RTC operating current	IRTC Notes 1, 2, 3					0.02		μΑ
12-bit interval timer operating current	IIT Notes 1, 2, 4					0.02		μΑ
Watchdog timer operating current	I _{WDT} Notes 1, 2, 5	fı∟ = 15 kHz				0.22		μА
A/D converter	IADC Notes 1, 6	When conversion	Normal mode,	AVREFP = VDD = 5.0 V		1.3	1.7	mA
operating current		at maximum speed	Low voltage m	node, AV _{REFP} = V _{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1					75.0		μΑ
Temperature sensor operating current	TMPS Note 1					75.0		μΑ
LVD operating current	ILVI Notes 1, 7					0.08		μΑ
Self- programming operating current	FSP Notes 1, 8					2.50	12.2	mA
Programmable	IPGA Note 9			AVREFP = VDD = 5.0 V		0.21	0.31	mA
gain amplifier operating current				AVREFP = VDD = 3.0 V		0.18	0.29	mA
Comparator	ICMP Note 10	When one compara	ator channel is	AVREFP = VDD = 5.0 V		41.4	62	μA
operating		operating		AVREFP = VDD = 3.0 V		37.2	59	μA
current	IVREF	When one internal	reference	AVREFP = VDD = 5.0 V		14.8	26	μΑ
		voltage circuit is op	erating	AVREFP = VDD = 3.0 V		8.9	20	μΑ
Programmable	IREF Note 11			AVREFP = VDD = 5.0 V		3.2	5.1	μΑ
gain amplifier/ comparator reference current source				AVREFP = VDD = 3.0 V		2.9	4.9	μΑ
BGO operating current	BGO ^{Note 12}					2.50	12.2	mA
SNOOZE	ISNOZ Note 1	ADC operation	The mode is p	erformed		0.50	1.1	mA
operating current		The A/D conversion operations are performed, Standard mode, AVREFP = VDD = 5.0 V				2.0	3.04	mA
		CSI/UART operatio				0.70	1.54	mA

(Notes and Remarks are listed on the next page.)

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- <R> Notes 1. Current flowing to the VDD.
 - 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip ocsillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and f_{IL} operating current). The current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode.
 - 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
 - **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
 - 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - 8. Current flowing during self-programming operation.
 - **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
 - **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
 - **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
 - 12. Current flowing only during data flash rewrite.
 - Remarks 1. fil.: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is T_A = 25°C
 - 5. Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AVREFP = VDD = 5.0 V)

ICMP × 3 + IVREF + IPGA + IREF
= 41.4
$$[\mu A]$$
 × 3 + 14.8 $[\mu A]$ × 1 + 210 $[\mu A]$ + 3.2 $[\mu A]$
= 352.2 $[\mu A]$

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AVREFP = VDD = 5.0 V)

ICMP × 2 + IREF
= 41.4
$$[\mu A]$$
 × 2 + 3.2 $[\mu A]$
= 86.0 $[\mu A]$

2.4 AC Characteristics

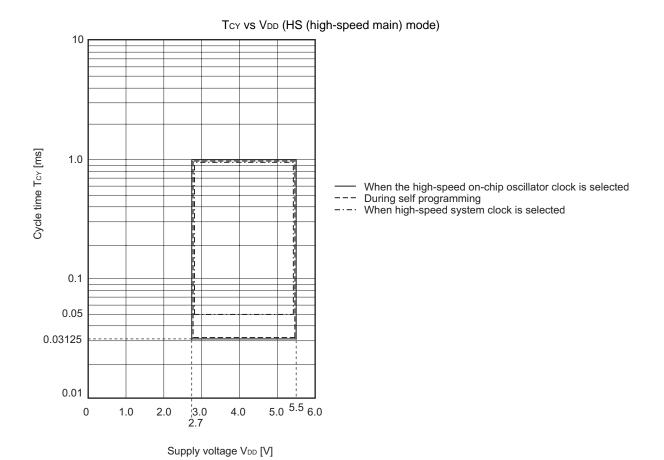
(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

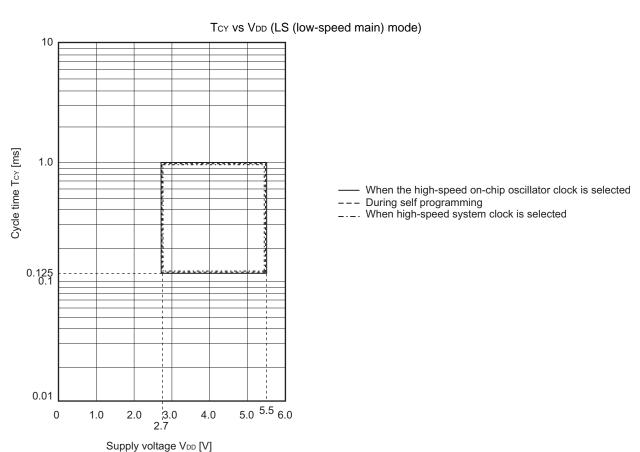
	Items	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
	Instruction cycle (minimum	Тсч	Main system	HS (high-s	speed	main) mode	0.03125		1	μS
	instruction execution time)			LS (low-sp main) mod		$T_A = -40 \text{ to } +85^{\circ}\text{C}$	0.125		1	μS
			Subsystem cl	ock (fsuв)	oper	ation	28.5	30.5	31.3	μS
			In the self	HS (high-s	speed	main) mode	0.03125		1	μS
			programming mode	LS (low-sp main) mod		$T_A = -40 \text{ to } +85^{\circ}\text{C}$	0.125		1	μS
	External system clock frequency	fex					1.0		20.0	MHz
<r></r>		fexs			32		35	kHz		
	External system clock input high-	texh, texl					24			ns
	level width, low-level width	texhs, texhs					13.7			μS
	TI03, TI05, TI06, TI07 input high- level width, low-level width	tтін, tтіL				2/fмск+10			ns	
	T003, T005, T006, TKB000,	fто	HS (high-spe	ed main)	4.0 \	$V \le V_{DD} \le 5.5 V$			8	MHz
	TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to		mode		2.7	V ≤ V _{DD} < 4.0 V			4	MHz
	TKCO05 output frequency (When duty = 50%)		LS (low-spee		4.0 \	$V \le V_{DD} \le 5.5 V$			4	MHz
	udiy = 3070)		mode, $T_A = -4$ +85°C	40 to	2.7	$V \le V_{DD} < 4.0 V$			2	MHz
	Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3, INTP4, INTP9 to INTP11, INTP20 to INTP23			1			μS	
	RESET low-level width	trsl					10			μs

Remark fmck: Timer array unit operation clock frequency

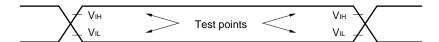
(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

<R>> Minimum Instruction Execution Time during Main System Clock Operation

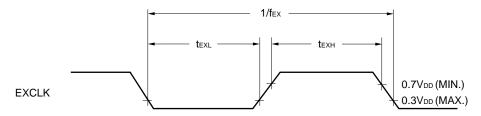




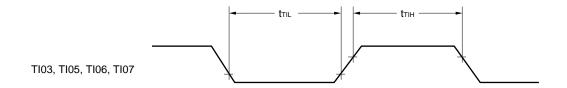
AC Timing Test Points

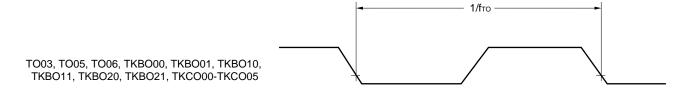


External System Clock Timing

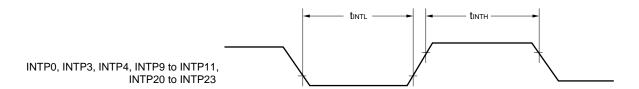


TI/TO Timing

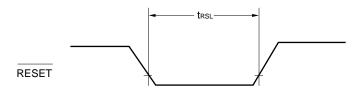




Interrupt Request Input Timing



RESET Input Timing



2.5 Peripheral Functions Characteristics

<R> 2.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.7 V≤ V _{DD}	2.7 V≤ V _{DD} ≤ 5.5 V		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 2		5.3		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

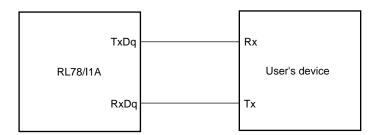
2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz ($2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$)

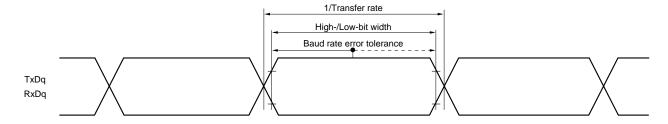
LS (low-speed main) mode: 8 MHz (2.7 V \leq V_{DD} \leq 5.5 V), TA = -40 to +85°C

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03))

<R> (2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (T_A = −40 to +105°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-s	peed main) ode	LS (low-sp	Unit	
			MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t KCY1	tkcy1 ≥ 4/fclk	125		500		ns
SCKp high-/low-level	t кн1,	$4.0~V \leq V_{DD} \leq 5.5~V$	tkcy1/2 - 12		tkcy1/2 - 50		ns
width	t KL1	$2.7~V \leq V_{DD} \leq 5.5~V$	tkcy1/2 - 18		tkcy1/2 - 50		ns
SIp setup time (to SCKp1)	tsıĸı	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	44		110		ns
Note 1		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	44		110		ns
SIp hold time (from SCKp↑) Note 2	tksi1		19		19		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note 4		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.
- **5**. Operating condtions of LS (low-speed main) mode is $T_A = -40$ to +85 °C.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))

<R> (3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbo	Conditions		` ` `	peed main) ode	LS (low-spee	Unit	
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	$4.0~V \le V_{DD} \le 5.5~V$	20 MHz < fмск	8/fмск				ns
Note 5			fмcк ≤ 20 MHz	6/fмск		6/ƒмск		ns
		$2.7~V \leq V_{DD} \leq 5.5~V$	16 MHz < fмск	8/fмск				ns
			fмcк ≤ 16 MHz	6/fмск		6/ƒмск		ns
SCKp high-/low-level width	tкн2, tкL2			tkcy2/2		tkcy2/2		ns
SIp setup time (to SCKp↑) Note 1	tsık2			1/fмск+20		1/fмск+30		ns
Slp hold time (from SCKp↑) Note 2	t _{KSI2}			1/fмск+31		1/fмск+31		ns
Delay time from SCKp↓ to SOp output Note 3	tkso2	C = 30 pF Note 4			2/fмск+ 44		2/fмск+ 110	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - 6. Operating condtions of LS (low-speed main) mode is T_A = -40 to +85 °C.

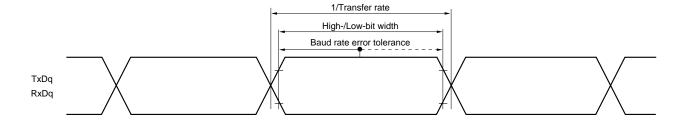
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

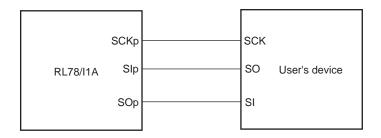
2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

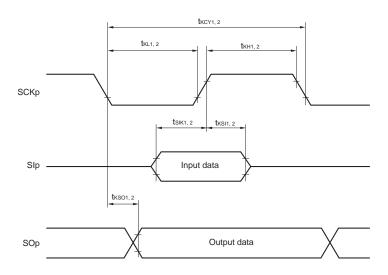
n: Channel number (mn = 00))



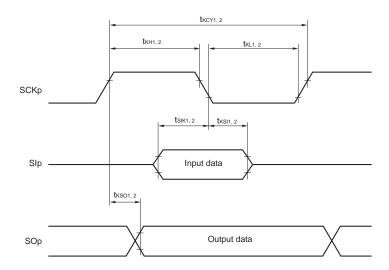
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)

<R> (4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol			Conditions	` •	HS (high-speed main) Mode		LS (low-speed main) Mode		
						MAX.	MIN.	MAX.		
Transfer		Recep-	4.0 V ≤	$V_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le V_b \le 4.0 \text{ V}$		fmck/6 Note 1		fmck/6 Note 1	bps	
rate		tion		Theoretical value of the maximum transfer rate fmck = fclk Note 2		5.3		1.3	Mbps	
			2.7 V ≤	$V_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le V_{b} \le 2.7 \text{ V}$		fmck/6 Note 1		fmck/6 Note 1	bps	
				Theoretical value of the maximum transfer rate fmck = fclk Note 2		5.3		1.3	Mbps	

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are:

HS (high-speed main) mode: 32 MHz ($2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$)

LS (low-speed main) mode: 8 MHz (2.7 V \leq V_{DD} \leq 5.5 V), T_A = -40 to +85 °C.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03)

<R>

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission		\leq V _{DD} \leq 5.5 V, \leq V _b \leq 4.0 V		Note 1		Note 1	bps
			2.7 V	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.8 Note 2		2.8 Note 2	Mbps
				≤ V _{DD} < 4.0 V, ≤ V _b ≤ 2.7 V		Note 3		Note 3	bps
				Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 Note 4		1.2 Note 4	Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{V}_{D} \le 4.0 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

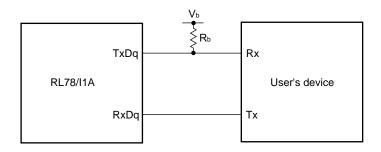
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- **5.** Operating condtions of LS (low-speed main) mode is $T_A = -40$ to +85 °C.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

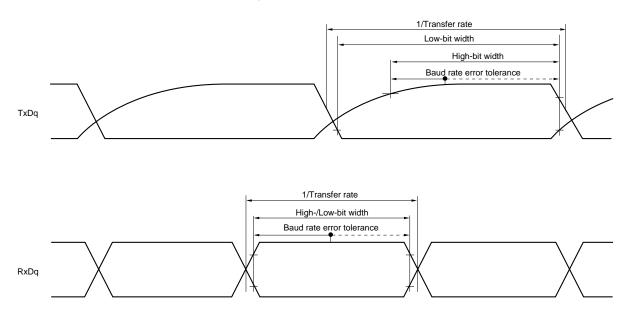


- Remarks 1. $R_b[\Omega]$:Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03))

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage
 - 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

<R> (5) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter Symb			Conditions	H		LS		Unit
			(high-spe		(low-speed main)		-	
				MIN.	MAX.	Mod MIN.	e MAX.	
001/2 20212 (222		0/1	407/47/4557/077/47/440		WAX.		WAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fcLk	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	200		1150		ns
			$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$					
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7$	300		1150		ns
			V,					
			$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$					
SCKp high-level	t кн1	4.0 V ≤ V _{DD} ≤	$\leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$	tkcy1/2 - 50		tkcy1/2 - 75		ns
width		C _b = 30 pF, I	$R_b = 1.4 \text{ k}\Omega$					
		$2.7 \text{ V} \leq \text{V}_{DD}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$	tkcy1/2 -		tkcy1/2 -		ns
		C _b = 30 pF, I	$R_b = 2.7 \text{ k}\Omega$	120		170		
SCKp low-level	t _{KL1}	4.0 V ≤ V _{DD} ≤	$\leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$	tkcy1/2 - 7		tkcy1/2 - 50		ns
width		C _b = 30 pF, I	$R_b = 1.4 \text{ k}\Omega$					
		$2.7 \text{ V} \leq \text{V}_{DD}$	$< 4.0 \ V, \ 2.3 \ V \le V_b \le 2.7 \ V,$	tkcy1/2 - 10		tkcy1/2 - 50		ns
		C _b = 30 pF, I	$R_b = 2.7 \text{ k}\Omega$					
SIp setup time	tsıĸ1	4.0 V ≤ V _{DD} ≤	$\leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$	81		479		ns
(to SCKp↑) Note 1		C _b = 30 pF, I	$R_b = 1.4 \text{ k}\Omega$					
		$2.7 \text{ V} \leq \text{V}_{DD}$	$< 4.0 \ V, \ 2.3 \ V \le V_b \le 2.7 \ V,$	177		479		ns
		C _b = 30 pF, I	$R_b = 2.7 \text{ k}\Omega$					
SIp hold time	t KSI1	4.0 V ≤ V _{DD} ≤	$\leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$	10		19		ns
(from SCKp↑) Note 1		C _b = 30 pF, I	$R_b = 1.4 \text{ k}\Omega$					
		$2.7 \text{ V} \leq \text{V}_{DD}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$	10		19		ns
		C _b = 30 pF, I	$R_b = 2.7 \text{ k}\Omega$					
Delay time from	t ks01	4.0 V ≤ V _{DD} ≤	$\leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$		60		100	ns
SCKp↓ to SOp output Note 1		C _b = 30 pF, I	$R_b = 1.4 \text{ k}\Omega$					
σαιραι		$2.7 \text{ V} \leq \text{V}_{DD}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$		130		195	ns
		C _b = 30 pF, I	$R_b = 2.7 \text{ k}\Omega$					
SIp setup time	tsıĸ1	4.0 V ≤ V _{DD} ≤	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq V_b \leq 4.0 \text{ V},$	44		110		ns
(to SCKp \downarrow) Note 2		C _b = 30 pF, I	$R_b = 1.4 \text{ k}\Omega$					
		$2.7 \text{ V} \leq \text{V}_{DD}$	$<4.0 \ V, \ 2.3 \ V \le V_b \le 2.7 \ V,$	44		110		ns
		C _b = 30 pF, I	$R_b = 2.7 \text{ k}\Omega$					
SIp hold time	t KSI1	4.0 V ≤ V _{DD} ≤	$\leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq V_b \leq 4.0 \text{ V},$	10		19		ns
(from SCKp↓)		C _b = 30 pF, I	$R_b = 1.4 \text{ k}\Omega$					
£		$2.7 \text{ V} \leq \text{V}_{DD}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$	10		19		ns
		C _b = 30 pF, I	$R_b = 2.7 \text{ k}\Omega$					
Delay time from	t KSO1	4.0 V ≤ V _{DD} ≤	$\leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq V_b \leq 4.0 \text{ V},$		10		25	ns
SCKp↑ to SOp output Note 2		C _b = 30 pF, I	$R_b = 1.4 \text{ k}\Omega$					
COP Output		$2.7 \text{ V} \leq \text{V}_{DD}$	$<4.0 \ V, \ 2.3 \ V \le V_b \le 2.7 \ V,$		10		25	ns
		C _b = 30 pF, I	$R_b = 2.7 \text{ k}\Omega$					

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

- 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. Operating condtions of LS (low-speed main) mode is $T_A = -40$ to +85 °C.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- **Remarks 1.** $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),g: PIM and POM number (g = 1)

<R> (6) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

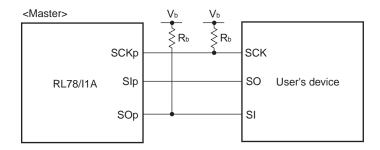
Parameter	Symbol		Conditions	HS (high-speed	d main) Mode	LS (low-speed	main) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$\label{eq:local_problem} \begin{split} 4.0 \ V & \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V & \leq V_{b} \leq 4.0 \ V, \end{split}$	300		1150		ns
			$C_b=30~pF,~R_b=1.4~k\Omega$					
			$\begin{split} 2.7 \text{ V} &\leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \\ 2.3 \text{ V} &\leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \end{split}$	500		1150		ns
			$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$					
SCKp high-level	t кн1	4.0 V ≤ V _{DD} :	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{Vb} \leq 4.0 \text{ V},$	tkcy1/2 - 75		tkcy1/2 - 75		ns
width		C _b = 30 pF,	$R_b = 1.4 \text{ k}\Omega$					
		$2.7 \text{ V} \leq \text{V}_{DD}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$	tксү1/2 – 170		tксү1/2 – 170		ns
		C _b = 30 pF,	$R_b = 2.7 \text{ k}\Omega$					
SCKp low-level	t KL1	4.0 V ≤ V _{DD} :	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$	tксү1/2 – 12		tkcy1/2 - 50		ns
width		C _b = 30 pF,	$R_b = 1.4 \text{ k}\Omega$					
		2.7 V ≤ V _{DD} ·	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$	tксү1/2 – 18		tксү1/2 – 50		ns
		C _b = 30 pF,	$R_b = 2.7 \text{ k}\Omega$					
SIp setup time	tsık1	4.0 V ≤ V _{DD} :	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$	81		479		ns
(to SCKp↑) Note 1		C _b = 30 pF,	$R_b = 1.4 \text{ k}\Omega$					
		2.7 V ≤ V _{DD} ·	< 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V,	177		479		ns
		C _b = 30 pF,	$R_b = 2.7 \text{ k}\Omega$					
Slp hold time	t KSI1	4.0 V ≤ V _{DD} :	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$	19		19		ns
(from SCKp↑)		C _b = 30 pF,	$R_b = 1.4 \text{ k}\Omega$					
		2.7 V ≤ V _{DD} •	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$	19		19		ns
		C _b = 30 pF,	$R_b = 2.7 \text{ k}\Omega$					
Delay time from	tkso1	4.0 V ≤ V _{DD} :	≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V,		100		100	ns
SCKp↓ to SOp output Note 1		C _b = 30 pF,	$R_b = 1.4 \text{ k}\Omega$					
oop output		2.7 V ≤ V _{DD} ·	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$		195		195	ns
		C _b = 30 pF,	$R_b = 2.7 \text{ k}\Omega$					
SIp setup time	tsık1	4.0 V ≤ V _{DD} :	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$	44		110		ns
(to SCKp↓) Note 2		C _b = 30 pF,	$R_b = 1.4 \text{ k}\Omega$					
		2.7 V ≤ V _{DD} ·	< 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V,	44		110		ns
		C _b = 30 pF,	$R_b = 2.7 \text{ k}\Omega$					
SIp hold time	t KSI1	4.0 V ≤ V _{DD} :	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$	19		19		ns
(from SCKp \downarrow)		Cb = 30 pF,	Rb = 1.4 kΩ					
		2.7 V ≤ V _{DD} ·	< 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V,	19		19		ns
		Cb = 30 pF,	$Rb = 2.7 k\Omega$					
Delay time from	tkso1	4.0 V ≤ V _{DD} :	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$		25		25	ns
SCKp↑ to SOp output Note 2		Cb = 30 pF,						
COP output			< 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V,		25		25	ns
		Cb = 30 pF,						

Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. Operating condtions of LS (low-speed main) mode is $T_A = -40$ to +85 °C.

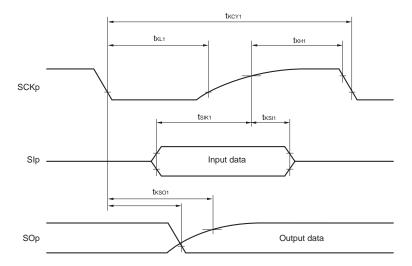
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

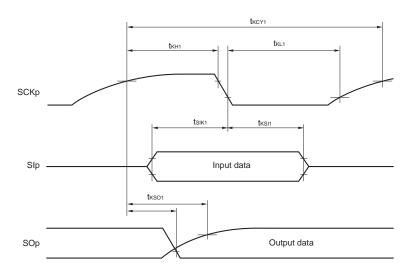


- **Remarks 1.** $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

<R> (7) DALI/UART4 mode

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate				fмск/12		fмск/12	bps
		Maximum transfer rate theoretical value HS: fclk = 32 MHz, fмck = fclk LS: fclk = 8 MHz, fмck = fclk		2.6		0.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register mn (SPS4).)

Caution Operating condtions of LS (low-speed main) mode is $T_A = -40$ to +85 °C.

<R>

2.5.2 Serial interface IICA

(1) I²C standard mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: fcLK≥ 1 MHz	0	100	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		4.7		μS
Hold time ^{Note 1}	thd:sta		4.0		4.0		μS
Hold time when SCLA0 = "L"	tLOW		4.7		4.7		μS
Hold time when SCLA0 = "H"	tніgн		4.0		4.0		μS
Data setup time (reception)	tsu:dat		250		250		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	3.45	μS
Setup time of stop condition	tsu:sto		4.0		4.0		μS
Bus-free time	t BUF		4.7		4.7		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- 3. Operating condtions of LS (low-speed main) mode is $T_A = -40$ to +85 °C.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$

<R> (2) I²C fast mode

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

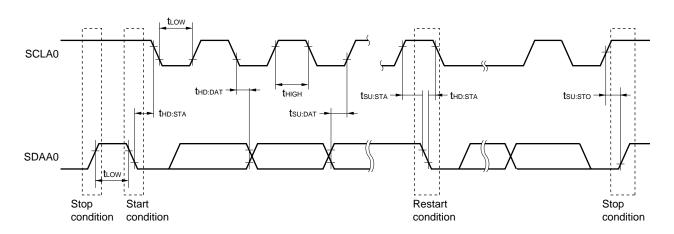
Parameter	Symbol	Conditions	HS (hig main)	h-speed Mode	LS (low main)		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	fast mode: fcLk ≥ 3.5 MHz	0	400	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		0.6		μS
Hold time ^{Note 1}	thd:STA		0.6		0.6		μS
Hold time when SCLA0 = "L"	tLOW		1.3		1.3		μS
Hold time when SCLA0 = "H"	tніgн		0.6		0.6		μS
Data setup time (reception)	tsu:dat		100		100		ns
Data hold time (transmission)Note 2	thd:dat		0	0.9	0	0.9	μS
Setup time of stop condition	tsu:sto		0.6		0.6		μS
Bus-free time	tBUF		1.3		1.3		μS

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
 - 3. Operating condtions of LS (low-speed main) mode is $T_A = -40$ to +85 °C.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



2.6 Analog Characteristics

<R> 2.6.1 A/D converter characteristics

<R> Classification of A/D converter characteristics

	Reference Voltage								
	Reference voltage (+) = AVREFP	Reference voltage (+) = V _{DD}	Reference voltage (+) = VBGR						
Input channel	Reference voltage (–) = AVREFM	Reference voltage (-) = Vss	Reference voltage (-) = AVREFM						
ANI0 to ANI2, ANI4 to ANI7	Refer to 2.6.1 (1) .	Refer to 2.6.1 (3) .	Refer to 2.6.1 (4) .						
ANI16 to ANI19	Refer to 2.6.1 (2) .								
Internal reference voltage	Refer to 2.6.1 (1) .		_						
Temperature sensor output									
voltage									

<R> (1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	s	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3			1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2, ANI4 to ANI7	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	3.1875		39	μS
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$	3.5625		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} Note 3				±0.25	%FSR
Full-scale error ^{Notes 1, 2}	E _F s	10-bit resolution AV _{REFP} = V _{DD} Note 3				±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} Note 3				±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3				±1.5	LSB
Analog input voltage	VAIN	ANI2, ANI4 to ANI7		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) mode)		V _{BGR} Note 4		V
		Temperature sensor output vo (HS (high-speed main) mode	•	\	/ _{TMPS25} Note	4	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%FSR$ to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

<R> (2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI16 to ANI19

(TA = -40 to +105°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} Notes 3			1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target ANI pin : ANI16 to ANI19	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} Notes 3				±0.35	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution AV _{REFP} = V _{DD} Notes 3				±0.35	%FSR
Integral linearity error ^{Note}	ILE	10-bit resolution AV _{REFP} = V _{DD} Notes 3				±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} Notes 3				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AV _{REFP}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When $AV_{REFP} \le V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

<R> (3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin : ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V}, \text{Reference voltage (+)} = V_{DD}, \text{ Reference voltage (-)} = V_{SS})$

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	3.1875		39	μS
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution				±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
Differential linearity error	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI2, ANI4 to ANI7	•	0		V_{DD}	V
		ANI16 to ANI19		0		V_{DD}	V
		Internal reference voltage (HS (high-speed main) mod	e)		V _{BGR} Note 3		V
		Temperature sensor output (HS (high-speed main) mode	•	\	/TMPS25 Note	3	V

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

<R>

<R> <R> (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

(TA = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V, Reference voltage (+) = V_{BGR} Note 3, Reference voltage (-) = AV_{REFM} = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv	8-bit resolution	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	Vain		0		V _{BGR} Note 3	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.
- **4.** When reference voltage (–) = Vss, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AVREFM.

<R> 2.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, T _A = +25°C		1.05		V
<r></r>	Internal reference voltage	V _{BGRT}	Setting ADS register = 81H	1.38	1.45	1.5	V
	Temperature coefficient	F _{VTMPS}	Temperature sensor that depends on the temperature		-3.6		mV/C
<r></r>	Operation stabilization wait time	tamp		5			μs



2.6.3 Programmable gain amplifier

(Ta = -40 to +105°C, 2.7 V \leq AVREFP = VDD \leq 5.5 V, Vss = AVREFM = 0 V)

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9V _{DD} /	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 time	16 times				±1.5	%
		32 times					±2	%
Slew rate ^{Note 1}	SRRPGA	- 3	$4.0~V \leq V_{DD} \leq 5.5~V$	4, 8 times	4			V/μs
	edge	edge		16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	4, 8 times	1.8			V/μs
				16, 32 times	0.5			V/μs
	SRFPGA	Falling	$4.0~V \leq V_{DD} \leq 5.5~V$	4, 8 times	3.2			V/μs
		edge		16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	4, 8 times	1.2			V/μs
				16, 32 times	0.5			V/μs
Operation stabilization wait time ^{Note 2}	t PGA	4, 8 times			5			μS
		16, 32 t	16, 32 times					μS

Notes 1. When VIPGA = 0.1VDD/gain to 0.9VDD/gain.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.

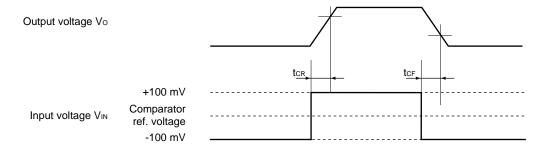
<R>

2.6.4 Comparator

(Ta = -40 to +105°C, 2.7 V \leq AVREFP = VDD \leq 5.5 V, Vss = AVREFM = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		V _{DD}	V
		СМРСОМ	0.045		0.9V _{DD}	V
Internal reference voltage deviation	△VIREF	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcf	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait time ^{Note 1}	tсмр	$3.3 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1			μS
		2.7 V ≤ V _{DD} < 3.3 V	3			μS
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 Note 2	10			μS

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - 2. Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.
- Remark These characteristics apply when AVREFP is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AVREFM is selected as GND of the internal reference voltage by using the CVRVS1 bit.



<R>

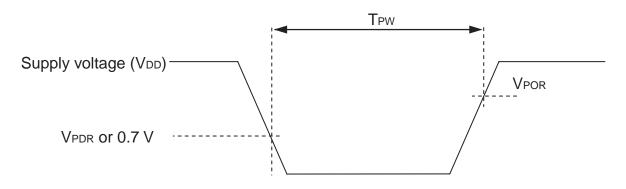
<R>

2.6.5 POR circuit characteristics

<R> (TA = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.45	1.51	1.57	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width ^{Note}	T _{PW}		300			μS

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interruput Mode ($T_A = -40$ to +105°C, $V_{PDR} \le V_{DD} \le 5.5$ V, $V_{SS} = 0$ V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _L VD0	Power supply rise time	3.97	4.06	4.14	V
voltage			Power supply fall time	3.89	3.98	4.06	V
		V _{LVD1}	Power supply rise time	3.67	3.75	3.82	V
			Power supply fall time	3.59	3.67	3.74	V
		V _{LVD2}	Power supply rise time	3.06	3.13	3.19	V
			Power supply fall time	2.99	3.06	3.12	V
		V _{LVD3}	Power supply rise time	2.95	3.02	3.08	V
			Power supply fall time	2.89	2.96	3.02	٧
		V _{LVD4}	Power supply rise time	2.85	2.92	2.97	V
			Power supply fall time	2.79	2.86	2.91	V
		V _{LVD5}	Power supply rise time	2.75	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
Minimum p	ulse width	tuw		300			μS
Detection of	delay time					300	μS

<R> LVD Detection Voltage of Interrupt & Reset Mode $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \leq V_{DD} \leq 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol		Cond	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _L VDD0	VPOC2, VPOC1, VPOC0 = (oc1, VPoc0 = 0, 1, 1, falling reset voltage: 2.7 V		2.70	2.75	2.81	V
mode	VLVDD1	LVIS1, LVIS0 =	= 1, 0	Rising release reset voltage	2.85	2.92	2.97	V
				Falling interrupt voltage	2.79	2.86	2.91	V
	VLVDD2	LVIS1, LVIS0 =	= 0, 1	Rising release reset voltage	2.95	3.02	3.08	V
				Falling interrupt voltage	2.89	2.96	3.02	V
	V _L VDD3	LVIS1, LVIS0 =	= 0, 0	Rising release reset voltage	3.97	4.06	4.14	V
				Falling interrupt voltage	3.89	3.98	4.06	V

<R> 2.6.7 Supply voltage rise inclination characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SVDD				54	V/ms

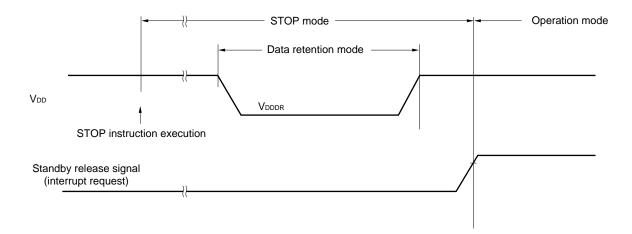
Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 2.4 AC Characteristics.

2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
<r></r>	Data retention supply voltage	V _{DDDR}		1.44 ^{Note}		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Condition	ons	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$2.7~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$		1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years	T _A = 85°C ^{Note 3}	1,000			Times
Number of data flash rewrites ^{Notes 1, 2, 3}		Retained for 1 year	T _A = 25°C ^{Note 3}		1,000,000		
		Retained for 5 years	T _A = 85°C ^{Note 3}	100,000			
		Retained for 20 years	T _A = 85°C ^{Note 3}	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

<R> 2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

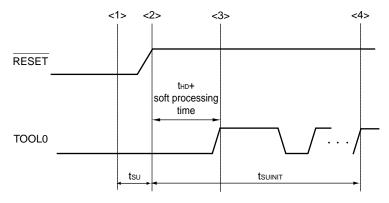
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps

<R>

2.10 Timing Specs for Switching Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μS
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends

thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

<R> 3. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +125°C)

Target products : $T_A = -40 \text{ to } +125^{\circ}\text{C}$

R5F1076CMSP#V0, R5F1076CMSP#X0, R5F107ACMSP#V0,R5F107ACMSP#X0, R5F107AEMSP#V0, R5F107AEMSP#X0, R5F107DEMSP#V0, R5F107DEMSP#X0

Cautions

- The RL78/I1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- 2. When any of these products are used at 105° C or lower, refer to "2. ELECTRICAL SPECIFICATIONS (T_A = -40 to $+105^{\circ}$ C)".



3.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	−0.3 to +2.8 and −0.3 to V _{DD} +0.3 ^{Note 1}	٧
Input voltage	VII	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo ₁	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	VAI1	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 4. Must be 6.5 V or lower.
 - **5.** Do not exceed $AV_{REF(+)} + 0.3 \text{ V}$ in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **2.** AV_{REF (+)}: + side reference voltage of the A/D converter.
- 3. Vss: Reference voltage

Absolute Maximum Ratings (T_A = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins -170 mA	P02, P03, P40, P120	-70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	Iон ₂	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins 170 mA	P02, P03, P40, P120	70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	lol2	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operation	on mode	-40 to +125	°C
temperature		In flash memory p	In flash memory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Recommended Circuit	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator	Vss X1 X2 Rd C1 — C2 —		1.0		20.0	MHz
XT1 clock frequency (fxt) ^{Note}	Crystal resonator	Vss XT2 XT1 Rd		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

3.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator clock frequency accuracyNote 2		$T_A = -20 \text{ to } 85^{\circ}\text{C}$	-1		+1	%
		$T_A = -40 \text{ to } 105^{\circ}\text{C}$	-1.5		+1.5	%
		$T_A = -40$ to 125°C When 16 MHz selected	-2		+2	%
Low-speed on-chip oscillator clock frequency	fıL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.

Remark When using the device at an ambient temperature that exceeds $T_A = 105$ °C, the selectable oscillation frequency is 16 MHz max..

3.2.3 PLL Characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	fpllin	High-speed system clock is selected (f _{MX} = 4 MHz)	3.92	4.00	4.08	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected (fiн = 4 MHz)	3.92	4.00	4.08	MHz
PLL output clock frequency ^{Note}	fPLL			fpllin × 16		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.

Remark When using the device at an ambient temperature that exceeds $T_A = 105$ °C, only 16 MHz (f_{PLL} x 1/4) can be selected as the CPU operating frequency.



3.3 DC Characteristics

3.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	І он1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{DD} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} < 4.0~\textrm{V}$			-1.0	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			-9.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			-3.0	mA
		Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty ≤ 70% Note 3)	$4.0~V \leq V_{DD} \leq 5.5~V$			-21.0	mA
			$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$			-6.0	mA
		Total of all pins	$4.0~V \leq V_{DD} \leq 5.5~V$			-21.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			-9.0	mA
	І он2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			-0.4	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	lol1	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{DD} \leq 5.5~V$			8.5 ^{Note 2}	mA
low ^{Note 1}		P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} < 4.0~\textrm{V}$			1.5 ^{Note 2}	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			20.0	mA
	(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			5.0	mA	
		P75 to P77, P147, P200 to P206 (When duty ≤ 70% Note 3)	$4.0~V \leq V_{DD} \leq 5.5~V$			20.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			10.0	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
lo _{L2}		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			15.0	mA
	lo _{L2}	Per pin for P20 to P22, P24 to P27	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			0.4 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$			1.6	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and lol = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8V _{DD}		VDD	>
	V _{IH2}	P03, P10, P11	TTL input buffer $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	2.1		V _{DD}	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$	2.0		V _{DD}	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		V _{DD}	V
Input voltage, low	V _{IL1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	V
	V _{IL2}	P03, P10, P11	TTL input buffer $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0		0.8	V
			TTL input buffer $3.3 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer $2.7 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}$	0		0.32	V

Caution The maximum value of ViH of pins P02, P10 to P12 is Vpp, even in the N-ch open-drain mode.

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	V _{DD} - 0.7			V
VoH2		P200 to P206	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OH1}} = -1.0 \text{ mA}$	V _{DD} - 0.5			٧
	V _{OH2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $\text{I}_{OH2} = -100 \ \mu\text{A}$	V _{DD} - 0.5			V
Output voltage, low	Vol1	P31, P40, P75 to P77, P120, P147, P200 to P206	$4.0~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V},$ $\textrm{IoL1} = 8.5~\textrm{mA}$			0.7	V
			$4.0~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V},$ $\textrm{IoL1} = 4.0~\textrm{mA}$			0.4	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $\text{IoL1} = 1.5 \text{ mA}$			0.4	V
	V _{OL2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $\text{Iol2} = 400 \ \mu\text{A}$			0.4	V

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Condition	ıs		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	Vi = Vpp				1	μA
	ILIH2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low	ILIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	Vı = Vss	Vı = Vss			-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pll-up resistance	R∪	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206		n input port	10	20	100	kΩ

3.3.2 Supply current characteristics

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V) (1/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	fih = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.8	mA
current ^{Note 1}		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		2.9	4.8	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Square wave input		3.2	5.6	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.7	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Square wave input		3.2	5.6	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.7	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Square wave input		2.0	3.3	mA
				VDD = 5.0 V	Resonator connection		2.0	3.3	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$ $V_{DD} = 3.0 \text{ V}$	Square wave input		2.0	3.3	mA
					Resonator connection		2.0	3.3	mA
	HS (high-	fiH = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		3.3	6.5	mA		
			speed main) mode ^{Note 5}	fPLL = 64 MHz, fcLK = 16 MHz	V _{DD} = 3.0 V		3.3	6.5	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 4} T _A = -40°C	Square wave input		4.2	6.0	μΑ
					Resonator connection		4.4	6.2	μΑ
				$f_{SUB} = 32.768 \text{ kHz}^{Note 4}$ $T_A = +25^{\circ}\text{C}$	Square wave input		4.2	6.0	μΑ
					Resonator connection		4.4	6.2	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μΑ
				$T_A = +50^{\circ}C$	Resonator connection		4.5	7.4	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μΑ
				T _A = +70°C	Resonator connection		4.6	8.3	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μΑ
				T _A = +85°C	Resonator connection		5.4	11.6	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μΑ
		T fs		T _A = +105°C	Resonator connection		7.1	21.0	μΑ
			fsub = 32.768 kHz ^{Note 4}	Square wave input		11.1	51.2	μΑ	
				T _A = +125°C	Resonator connection		11.3	51.4	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$ to 20 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(Ta = -40 to +125°C, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	DD2 Note 2	HALT	HS (high-	fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.50	2.0	mA
Current Note 1	Note 2	mode	speed main) mode ^{Note 7}		VDD = 3.0 V		0.50	2.0	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.40	2.2	mA
			speed main) mode ^{Note 7}	V _{DD} = 5.0 V	Resonator connection		0.50	2.3	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.40	2.2	mA
				V _{DD} = 3.0 V	Resonator connection		0.50	2.3	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.24	1.22	mA
			V _{DD} = 5.0 V	Resonator connection		0.30	1.28	mA	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.24	1.22	mA
				V _{DD} = 3.0 V	Resonator connection		0.30	1.28	mA
		HS (high- speed main)	$f_{IH} = 4 \text{ MHz}^{Note 4}$ $f_{PLL} = 64 \text{ MHz}, f_{CLK} = 16 \text{ MHz}$	V _{DD} = 5.0 V		0.95	3.7	mA	
			mode ^{Note 7} Subsystem clock operation	TPLL = 64 MIHZ, TCLK = 16 MIHZ	V _{DD} = 3.0 V		0.95	3.7	mA
				fsub = 32.768 kHz ^{Note 5} T _A = -40°C	Square wave input		0.28	0.70	μA
					Resonator connection		0.47	0.89	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.33	0.70	μА
				T _A = +25°C	Resonator connection		0.52	0.89	μА
				$f_{SUB} = 32.768 \text{ kHz}^{\text{Note 5}}$ $T_A = +50^{\circ}\text{C}$	Square wave input		0.41	1.90	μА
					Resonator connection		0.60	2.09	μΑ
				fsuB = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.54	2.80	μА
					Resonator connection		0.73	2.99	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.27	6.10	μА
				T _A = +85°C	Resonator connection		1.46	6.29	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		3.04	15.5	μA
				T _A = +105°C	Resonator connection		3.23	15.7	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		7.20	45.2	μA
				T _A = +125°C	Resonator connection		7.53	45.5	μА
	IDD3 ^{Note 6}	STOP . Note 8	T _A = -40°C				0.18	0.50	μА
		mode ^{Note 8}	T _A = +25°C				0.23	0.50	μА
			T _A = +50°C				0.27	1.70	μA
			T _A = +70°C				0.44	2.60	μA
			T _A = +85°C				1.17	5.90	μA
		T _A = +105°C				2.94	15.3	μA	
			$T_A = +125$ °C on the next p				7.14	45.1	μA

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 20 MHz
 - 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Condition	ons	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	IFIL Note 1					0.20		μΑ
RTC operating current	IRTC Notes 1, 2, 3					0.02		μА
12-bit interval timer operating current	I _{IT} Notes 1, 2, 4					0.02		μА
Watchdog timer operating current	WDT Notes 1, 2, 5	fı∟ = 15 kHz				0.22		μА
A/D converter operating current	IADC Notes 1, 6	When conversion at maximum speed Normal mode, AV _{REFP} = V _{DD} = 5.0 V				1.3	1.7	mA
A/D converter reference voltage current	IADREF Note 1					75.0		μА
Temperature sensor operating current	ITMPS ^{Note 1}					75.0		μΑ
LVD operating current	LVI Notes 1, 7					0.08		μА
Self- programming operating current	IFSP Notes 1, 8					2.5	12.2	mA
Programmable	IPGA Note 9			AVREFP = VDD = 5.0 V		0.21	0.37	mA
gain amplifier operating current				AVREFP = VDD = 3.0 V		0.18	0.35	mA
Comparator	ICMP Note 10	When one compara	ator channel is	AVREFP = VDD = 5.0 V		41.4	74	μА
operating		operating		AVREFP = VDD = 3.0 V		37.2	71	μА
current	IVREF	When one internal	reference	AVREFP = VDD = 5.0 V		14.8	31	μА
		voltage circuit is op	erating	AVREFP = VDD = 3.0 V		8.9	24	μА
Programmable	IREF Note 11			AVREFP = VDD = 5.0 V		3.2	6.1	μΑ
gain amplifier/ comparator reference current source				AVREFP = VDD = 3.0 V		2.9	4.9	μΑ
BGO operating current	BGO ^{Note 12}					2.50	12.2	mA
SNOOZE	ISNOZ Note 1	A/D converter	The mode is pe	erformed		0.50	1.10	mA
		operation		rsion operations are rmal mode, AV _{REFP} = V _{DD} = 5.0		1.20	2.17	mA
		CSI/UART operation	on			0.70	1.27	mA

(Notes and Remarks are listed on the next page.)

- Notes 1. Current flowing to the VDD.
 - 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operating mode or in HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and fill operating current). The current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
 - 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IWDT, when fclk = fsub when the watchdog timer is operating.
 - **6.** Current flowing only to the A/D converter. The supply current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC}, when the A/D converter is operating in operating mode or in HALT mode.
 - 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of ldd, ldd or ldd and llvd when the LVD circuit is in operation.
 - 8. Current flowing during self-programming operation.
 - **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
 - **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
 - **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
 - 12. Current flowing only during data flash rewrite.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$
 - 5. Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AVREFP = VDD = 5.0 V)

```
ICMP × 3 + IVREF + IPGA + IREF 
= 41.4 [\mu A] × 3 + 14.8 [\mu A] × 1 + 210 [\mu A] + 3.2 [\mu A] 
= 352.2 [\mu A]
```

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AVREFP = VDD = 5.0 V)

ICMP × 2 + IIREF = 41.4 $[\mu A]$ × 2 + 3.2 $[\mu A]$ = 86.0 $[\mu A]$

3.4 AC Characteristics

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

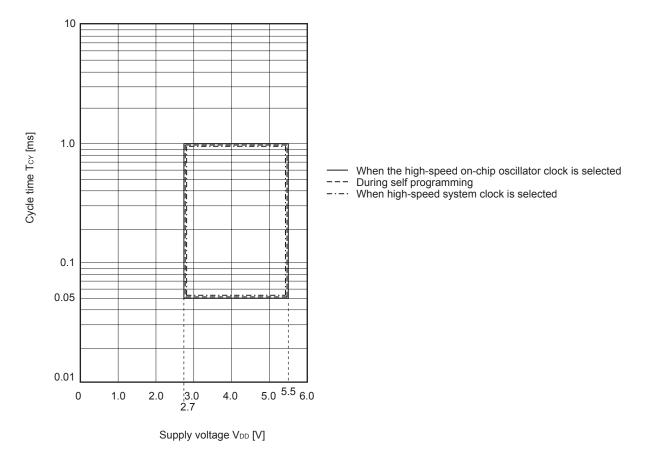
Items	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсч	Main system clock (fmain) operation HS (high-speed main) mode		0.05		1	μs
		Subsystem clock (fsub)	operation	28.5	30.5	31.3	μS
		In the self programming main) mode		0.05		1	μS
External system clock frequency	fex	·		1.0		20.0	MHz
	fexs			32		35	kHz
External system clock input high-	texh, texl		24			ns	
level width, low-level width	texhs, texhs		13.7			μS	
TI03, TI05, TI06, TI07 input high- level width, low-level width	tтıн, tтı∟			2/fмск+10			ns
TO03, TO05, TO06, TKBO00,	fто	HS (high-speed main)	$4.0~V \leq V_{DD} \leq 5.5~V$			5	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to TKCO05 output frequency (When duty = 50%)		mode	2.7 V ≤ V _{DD} < 4.0 V			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3, INTP4, INTP9 to INTP11, INTP20 to INTP23	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	1	_		μs
RESET low-level width	trsL			10			μS

Remark fmck: Timer array unit operation clock frequency

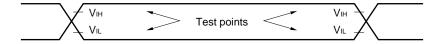
(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation

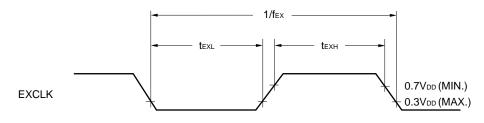
Tcy vs VDD (HS (high-speed main) mode)



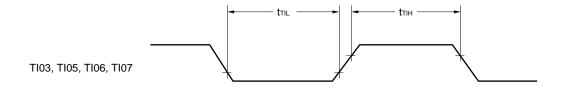
AC Timing Test Points

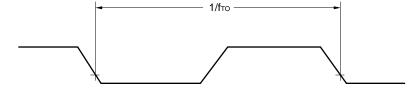


External System Clock Timing



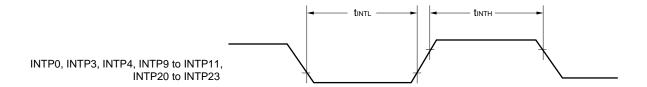
TI/TO Timing



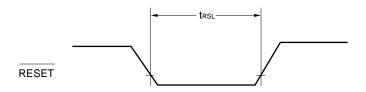


T003, T005, T006, TKB000, TKB001, TKB010, TKB011, TKB020, TKB021, TKC000 to TKC005

Interrupt Request Input Timing



RESET Input Timing



3.5 Peripheral Functions Characteristics

3.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

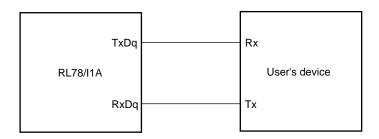
(1) During communication at same potential (UART mode) (dedicated baud rate generator output)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

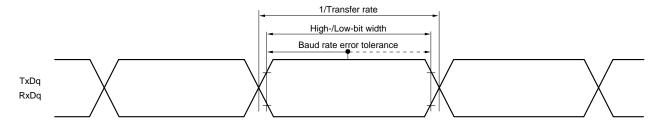
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Transfer rate Note		$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$				fмск/6	bps
			Theoretical value of the maximum transfer rate			3.3	Mbps
			fclk = 20 MHz, fmck = fclk				

Note Transfer rate in the SNOOZE mode is max. 9600 bps, min. 4800 bps.

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		` ` .	HS (high-speed main) Mode	
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0~V \leq V_{DD} \leq 5.5~V$	250		ns
			$2.7~V \leq V_{DD} \leq 5.5~V$	500		ns
SCKp high-/low-level width	t кн1,	4.0 V ≤ V _{DD} ≤ 5.5 V		tkcy1/2 - 20		ns
	t _{KL1}	$2.7~V \leq V_{DD} \leq 5.5~V$		tксү1/2 - 40		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsik1	$4.0~V \leq V_{DD} \leq 5.5$	V	80		ns
		$2.7~V \leq V_{DD} \leq 5.5~V$		80		ns
SIp hold time (from SCKp↑) ^{Note 2}	t _{KSI1}			40		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	t KSO1	C = 30 pF ^{Note 4}			80	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (q = 1)

fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		` •	HS (high-speed main) Mode	
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	tkcy2	$4.0~V \leq V_{DD} \leq 5.5~V$	fмcк ≤ 20 MHz	6/fмск		ns
		$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	16 MHz < fмск	8/fмск		ns
			fмск ≤ 16 MHz	6/ƒмск		ns
SCKp high-/low-level width	tkH2,			tkcy2/2		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsık2			1/fмск+40		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск+60		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso2	C = 30 pF ^{Note 4}			2/fмск+80	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

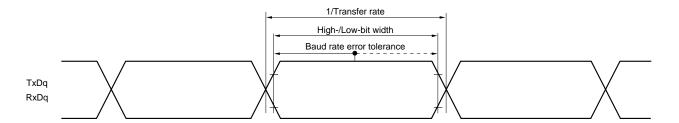
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

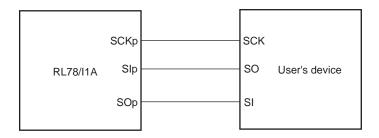
2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

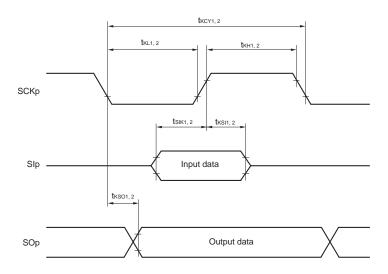
n: Channel number (mn = 00))



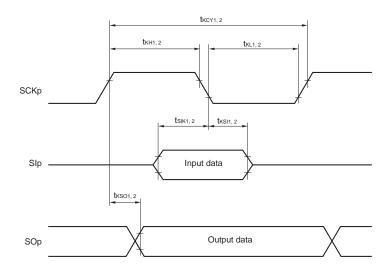
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2) $(T_A = -40 \text{ to } +125^{\circ}\text{C}, \ 2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \ \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions				Unit
					MIN.	MAX.	
Transfer rate		Reception	$4.0~V \leq V_{DD} \leq 5.5~V,$			fmck/6 ^{Note 1}	bps
			$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$			fmck/6 ^{Note 1}	bps
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps

- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 20 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. V_b[V]: Communication line voltage

- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions			HS (high-speed main) Mode	
					MIN.	MAX.	
Transfer rate		Transmission	$4.0~V \leq V_{DD} \leq 5.5~V,$			Note 1	bps
			$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, \ R_b = 1.4 \ k\Omega, \ V_b = 2.7 \ V$		2.8 ^{Note 2}	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$			Note 3	bps
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$		1.2 ^{Note 4}	Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq VDD \leq 5.5 V and 2.7 V \leq Vb \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

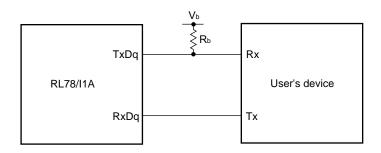
- 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

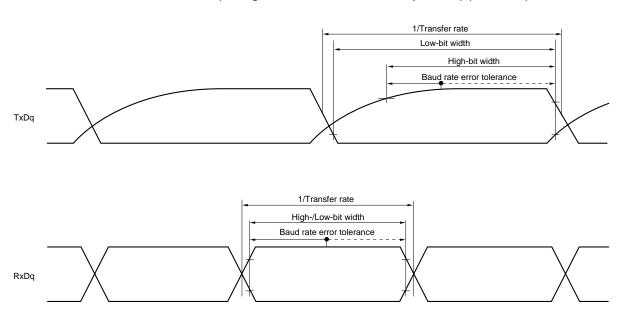
m: Unit number, n: Channel number (mn = 00 to 03))



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, V_b[V]: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

(5) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-sp	-	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ \begin{aligned} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	600		ns
			$ 2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, $ $ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega $	1000		ns
SCKp high-level width	t _{KH1}	$4.0 \text{ V} \leq \text{V}_{\text{DD}}$ $C_{\text{b}} = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq V_b \leq 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	tксү1/2 – 80		ns
		$2.7~V \leq V_{DD}$ $C_b = 30~pF,$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, $R_b = 2.7 \; k\Omega$	tксү1/2 — 17 0		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \leq \text{V}_{\text{DD}}$ $C_{\text{b}} = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	tксү1/2 – 28		ns
		$2.7~V \leq V_{DD}$ $C_b = 30~pF,$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, $R_b = 2.7 \; k\Omega$	tксү1/2 – 40		ns
SIp setup time (to SCKp↑) ^{Note 1}			$\leq 5.5 \ V, 2.7 \ V \leq V_b \leq 4.0 \ V,$ $R_b = 1.4 \ k\Omega$	160		ns
		$2.7~V \leq V_{DD}$ $C_b = 30~pF,$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, $R_b = 2.7 \; k\Omega$	250		ns
SIp hold time (from SCKp↑) ^{Note 1}	t _{KSI1}	$4.0 \text{ V} \leq \text{V}_{DD}$ $C_b = 30 \text{ pF},$	$\leq 5.5 \; \text{V}, 2.7 \; \text{V} \leq \text{V}_b \leq 4.0 \; \text{V},$ $R_b = 1.4 \; k\Omega$	40		ns
		$2.7~V \leq V_{DD}$ $C_b = 30~pF,$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, $R_b = 2.7 \; k\Omega$	40		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$4.0 \text{ V} \leq V_{DD}$ $C_b = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_\text{b} \leq 4.0 \text{ V},$ $R_\text{b} = 1.4 \text{ k}\Omega$		160	ns
		$2.7~V \leq V_{DD}$ $C_b = 30~pF,$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω		250	ns
SIp setup time (to $SCKp \downarrow$) ^{Note 2}	tsıĸı	$4.0 \text{ V} \leq \text{V}_{DD}$ $C_b = 30 \text{ pF},$	≤ 5.5 V, 2.7 V \leq Vb ≤ 4.0 V, R_b = 1.4 $k\Omega$	80		ns
		$2.7~V \leq V_{DD}$ $C_b = 30~pF,$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, $R_b = 2.7 \; k\Omega$	80		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksi1	$4.0 \text{ V} \leq \text{V}_{DD}$ $C_b = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	40		ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ $C_{\text{b}} = 30 \text{ pF},$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, $R_b = 2.7 \; k\Omega$	40		ns
Delay time from SCKp↑ to SOp outputNote 2	tkso1	$4.0 \text{ V} \leq \text{V}_{\text{DD}}$ $C_{\text{b}} = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq V_b \leq 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$		80	ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ $C_{\text{b}} = 30 \text{ pF},$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 k Ω		80	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

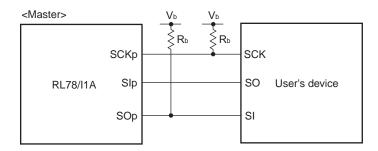
2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remark are listed on the next page.)



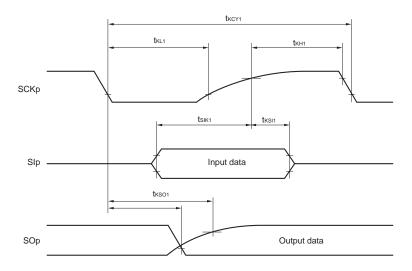
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

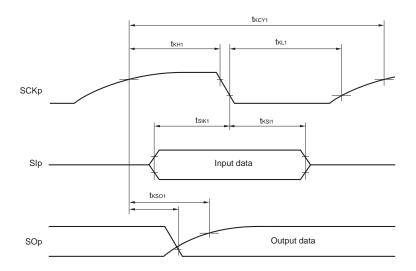


- **Remarks 1.** $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

(6) DALI/UART4 mode

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
Transfer rate				fмск/12	bps
		Maximum transfer rate theoretical value fclk = 20 MHz, fmck = fclk		1.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register 4 (SPS4).)

3.5.2 Serial interface IICA

(1) I2C standard mode

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	` `	h-speed Mode	Unit
			MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: fcLk≥ 1 MHz	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		μS
Hold time ^{Note 1}	thd:STA		4.0		μS
Hold time when SCLA0 = "L"	tLOW		4.7		μS
Hold time when SCLA0 = "H"	tніgн		4.0		μS
Data setup time (reception)	tsu:dat		250		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	μS
Setup time of stop condition	tsu:sто		4.0		μS
Bus-free time	t BUF		4.7		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \ pF, R_b = 2.7 \ k\Omega$

(2) I2C fast mode

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

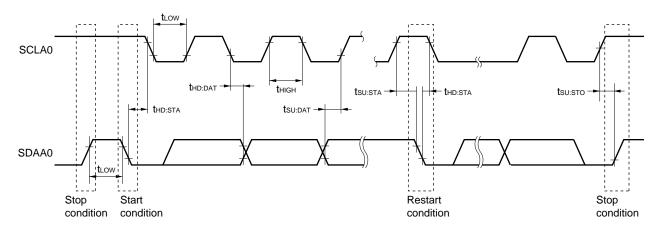
Parameter	Symbol	Conditions	HS (high-spee		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fscL	fast mode: fclk≥ 3.5 MHz	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		μS
Hold time ^{Note 1}	thd:STA		0.6		μS
Hold time when SCLA0 = "L"	tLOW		1.3		μS
Hold time when SCLA0 = "H"	thigh		0.6		μS
Data setup time (reception)	tsu:dat		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	0.9	μS
Setup time of stop condition	tsu:sto		0.6		μS
Bus-free time	t BUF		1.3		μS

- **Notes 1.** The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = V _{DD}	Reference voltage (+) = VBGR
Input channel	Reference voltage (–) = AVREFM	Reference voltage (-) = Vss	Reference voltage (-) = AVREFM
ANI0 to ANI2, ANI4 to ANI7	Refer to 3.6.1 (1) .	Refer to 3.6.1 (3) .	Refer to 3.6.1 (4) .
ANI16 to ANI19	Refer to 3.6.1 (2) .		
Internal reference voltage	Refer to 3.6.1 (1) .		_
Temperature sensor output			
voltage			

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +125°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Unit		
Resolution	RES			8		10	bit		
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3			1.2	±3.5	LSB		
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS		
		Target pin: ANI2, ANI4 to ANI7	$2.7~V \leq V_{DD} \leq 5.5~V$	3.4		39	μS		
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS		
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.7 V ≤ VDD ≤ 5.5 V	3.8		39	μs		
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} Note 3				±0.25	%FSR		
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution AV _{REFP} = V _{DD} Note 3				±0.25	%FSR		
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} Note 3				±2.5	LSB		
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3				±1.5	LSB		
Analog input voltage	Vain	ANI2, ANI4 to ANI7		0	V _{BGR} Note 4	AVREFP	V		
		Internal reference voltage (HS (high-speed main) mode)			V				
		Temperature sensor output vo (HS (high-speed main) mode	emperature sensor output voltage			V _{TMPS25} Note 4			

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19

(TA = -40 to +125°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	ons	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AVREFP = VDD Note 3				±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	2.125		39	μs
		Target ANI pin : ANI16 to ANI19	$2.7 \text{ V} \leq \text{V}_{DD} < 5.5 \text{ V}$	3.4		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AVREFP = VDD Note 3			±0.35	%FSR	
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution AVREFP = VDD Note 3				±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AVREFP = VDD Note 3				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AVREFP = VDD ^{Note 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AV _{REFP}	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.2\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V}, \text{ Reference voltage (+)} = V_{DD}, \text{ Reference voltage (-)} = V_{SS})$

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	3.4		39	μS
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.7 V ≤ V _{DD} ≤ 5.5 V	3.8		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution				±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution				±4.0	LSB
Differential linearity error Note	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI2, ANI4 to ANI7	7	0		V_{DD}	٧
		ANI16 to ANI19		0		V _{DD}	V
		Internal reference voltage (HS (high-speed main) mod	V _{BGR} Note 3			V	
		Temperature sensor output (HS (high-speed main) mode	emperature sensor output voltage				V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VBGR^{Note 3}, Reference voltage (-) = AVREFM Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv	8-bit resolution	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	Vain		0		VBGR Note 3	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.
- **4.** When reference voltage (–) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AVREFM.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AVREFM.

3.6.2 Temperature sensor characteristics

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, T _A = +25°C		1.05		V
Reference output voltage	VCONST	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	t AMP				5	μS

3.6.3 Programmable gain amplifier

(Ta = -40 to +125°C, 2.7 V \leq AVREFP = VdD ≤ 5.5 V, Vss = AVREFM = 0 V)

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9V _{DD} /	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 time	S				±1.5	%
		32 time	S				±2	%
Slew rate ^{Note 1}	SRRPGA	Rising edge	$4.0~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	4, 8 times	4			V/μs
				16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	4, 8 times	1.8			V/μs
				16, 32 times	0.5			V/μs
	SR _{FPGA}	Falling	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	4, 8 times	3.2			V/μs
		edge		16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	4, 8 times	1.2			V/μs
				16, 32 times	0.5			V/μs
Operation stabilization wait time ^{Note 2}	t PGA	4, 8 times			5			μS
		16, 32 t	imes		10			μS

Notes 1. When $V_{IPGA} = 0.1V_{DD}/gain$ to $0.9V_{DD}/gain$.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.

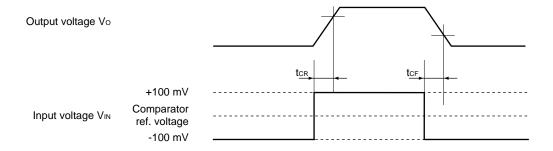
3.6.4 Comparator

(Ta = -40 to +125°C, 2.7 V \leq AVREFP = VDD \leq 5.5 V, Vss = AVREFM = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		V _{DD}	V
		СМРСОМ	0.045		0.9V _{DD}	V
Internal reference voltage deviation	△VIREF	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcf	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait time ^{Note 1}	tсмр	$3.3~V \leq V_{DD} \leq 5.5~V$	1			μS
		2.7 V ≤ V _{DD} < 3.3 V	3			μS
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 Note 2	10			μS

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - 2. Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.

Remark These characteristics apply when AVREFP is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AVREFM is selected as GND of the internal reference voltage by using the CVRVS1 bit.

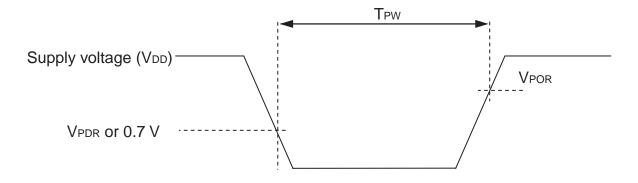


3.6.5 POR circuit characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.45	1.51	1.62	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.61	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interruput Mode

(TA = -40 to +125°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _{LVD0}	Power supply rise time	3.97	4.06	4.25	V
voltage			Power supply fall time	3.89	3.98	4.15	V
		V _{LVD1}	Power supply rise time	3.67	3.75	3.93	V
			Power supply fall time	3.59	3.67	3.83	V
		V _{LVD2}	Power supply rise time	3.06	3.13	3.28	V
			Power supply fall time	2.99	3.06	3.20	V
		V _{LVD3}	Power supply rise time	2.95	3.02	3.17	V
			Power supply fall time	2.89	2.96	3.09	V
		V _{LVD4}	Power supply rise time	2.85	2.92	3.07	V
			Power supply fall time	2.79	2.86	2.99	V
		V _{LVD5}	Power supply rise time	2.75	2.81	2.95	V
		Power supply fall time	2.70	2.75	2.88	V	
Minimum pu	ulse width	tuw		300			μS
Detection de	elay time					300	μS

LVD Detection Voltage of Interrupt & Reset Mode

(Ta = -40 to +125°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _L VDD0	V _{POC2} ,	VPOC1, VPOC0 = 0, 1, 1,	2.70	2.75	2.88	V	
mode	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	3.07	V
				Falling interrupt voltage	2.79	2.86	2.99	٧
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.17	٧
				Falling interrupt voltage	2.89	2.96	3.09	٧
	V _L VDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.25	V
				Falling interrupt voltage	3.89	3.98	4.15	V

3.6.7 Supply voltage rise inclination characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SVDD				54	V/ms

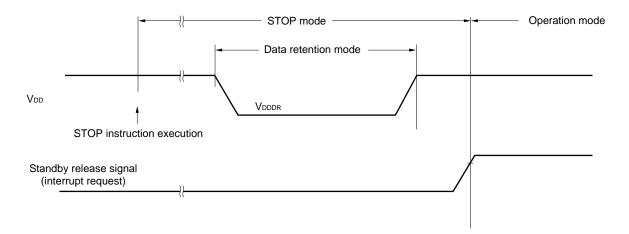
Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 3.4 AC Characteristics.

3.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.47 ^{Note}		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



3.8 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$		1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years	T _A = 85°C ^{Note 3}	1,000			Times
Number of data flash rewrites ^{Notes 1, 2, 3}		Retained for 1 year	T _A = 25°C ^{Note 3}		1,000,000		
		Retained for 5 years	T _A = 85°C ^{Note 3}	100,000			
		Retained for 20 years	T _A = 85°C ^{Note 3}	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

3.9 Dedicated Flash Memory Programmer Communication (UART)

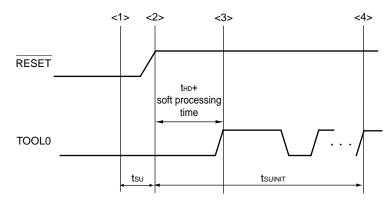
 $T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V}$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps

3.10 Timing Specs for Switching Flash Memory Programming Modes

 $T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V}$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends

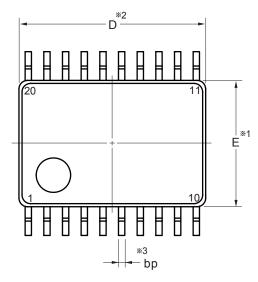
thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

4. PACKAGE DRAWINGS

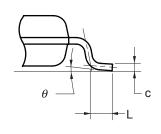
<R> 4.1 20-pin products

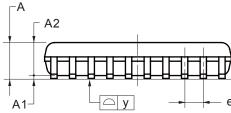
R5F1076CGSP#V0, R5F1076CGSP#X0, R5F1076CMSP#V0, R5F1076CMSP#X0

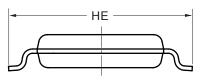
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



detail of lead end







(UNIT:mm)

ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
Α	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	0.22 ± 0.10
С	$0.15 + 0.05 \\ -0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°

1.Dimensions "※1" and "※2" do not include mold flash.2.Dimension "※3" does not include trim offset.

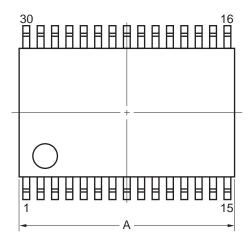
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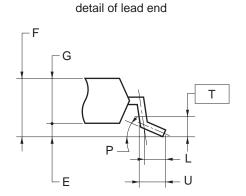
NOTE

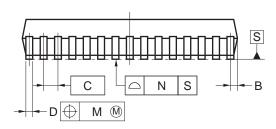
4.2 30-pin products

R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0, R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

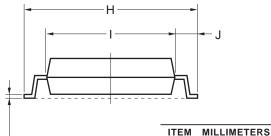






NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



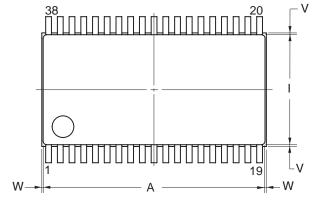
IIEW	MILLIMETERS
Α	9.85±0.15
В	0.45 MAX.
С	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
Е	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
- 1	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
М	0.13
N	0.10
Р	3°+5°
Т	0.25
U	0.6±0.15
	•

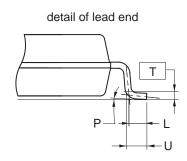
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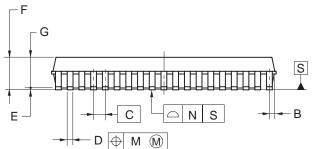
4.3 38-pin products

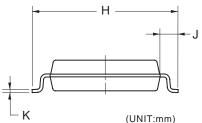
R5F107DEGSP#V0, R5F107DEGSP#X0, R5F107DEMSP#V0, R5F107DEMSP#X0

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-SSOP38-6.1x12.3-0.65	PRSP0038JA-B	P38MC-65-GAA-2	0.3









NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition .

	(UNIT:mm)
ITEM	DIMENSIONS
Α	12.30±0.10
В	0.30
С	0.65 (T.P.)
D	$0.30^{+0.10}_{-0.05}$
Е	0.125±0.075
F	2.00 MAX.
G	1.70±0.10
Н	8.10±0.20
1	6.10±0.10
J	1.00±0.20
K	$0.15^{+0.10}_{-0.05}$
L	0.50
М	0.10
Ν	0.10
Р	3°+5° -3°
T	0.25(T.P.)
U	0.60±0.15
V	0.25 MAX.
W	0.15 MAX.

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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SALES OFFICES

Renesas Electronics Corporation

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Renesas Electronics America Inc. 2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Milliboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Ha Tel: +86-10-8235-1155, Fax: +86-10-8235-7679 nunLu Haidian District. Beijing 100083. P.R.China

Renesas Electronics (Shanghal) Co., Ltd.
Unit 204, 205, AZIA Center, No. 1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: 486-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2868-9318, Fax: +852-2868-9022/9044

Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei, Taiwan Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.

тинивова специонизь манаузна эцп. Бли.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd. 11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea Tel: 482-2-588-3737, Fax: 482-2-588-5141